



100V 175°C PNP LOW SAT HIGH POWER TRANSISTOR IN POWERDI5060-8

Features

- $BV_{CEO} > -100V$
- I_C = -3A Continuous Collector Current
- I_{CM} = -8A Peak Pulse Current
- $R_{CE(SAT)} = 110m\Omega$ (typ)
- Rated to +175°C—Ideal for High Ambient Temperature **Environments**
- Complementary Part DXTN3C100PS
- Meets Requirements of Automotive Applications
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

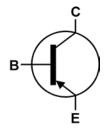
- Case: Power®DI5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Finish—Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)

Applications

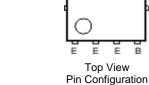
- **Power Management**
- Load Switch
- Linear Mode Voltage Regulator
- **Backlighting Applications**







Internal Schematic



C C

Top View **Bottom View**

Ordering Information

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DXTP3C100PSQ-13	Automotive	DXTP3C100PS	13	12	2500

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + CI) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.

Marking Information



DXTP3 = Product Type Marking Code C100PS = Product Type Marking Code YYWW = Date Code Marking YY = Last Digit of Year (ex: 18 = 2018) WW = Week Code (01 to 53)



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-100	V
Collector-Emitter Voltage	V _{CEO}	-100	V
Emitter-Base Voltage	V _{EBO}	-7	V
Base Current	I _B	-0.5	Α
Continuous Collector Current	Ic	-3	Α
Peak Pulse Collector Current	I _{CM}	-8	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	P _D	5	W	
Thermal Decistance, Junetian to Ambient	(Note 5)	Б	40	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\Theta JA}$	120		
Thermal Decistance, Junetica to Cons	(Note 5, 7)	Б	2	°C/W	
Thermal Resistance, Junction to Case	(Note 6, 7)	R _{eJC}	12		
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C	

ESD Ratings (Note 8)

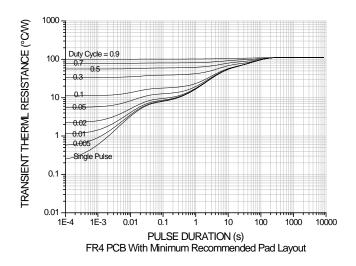
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge—Human Body Model	ESD HBM	V0008	V	3A
Electrostatic Discharge—Machine Model	ESD MM	400V	V	С

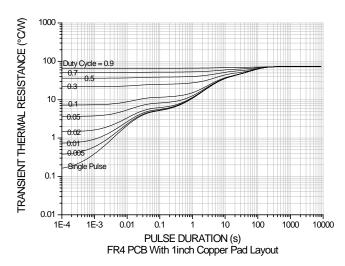
Notes:

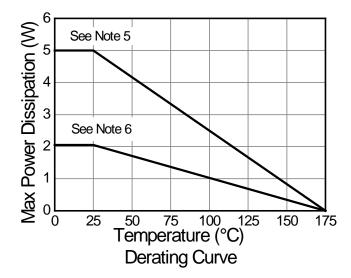
- 5. For a device mounted with the collector lead on 25mm × 25mm 2oz copper, on a single-sided 1.6mm FR4 PCB; the device is measured under still air conditions while operating in a steady state.
- 6. Same as Note 5 except mounted on minimum recommended pad layout.
- 7. Thermal resistance from junction to the top of the case.
- 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Typical Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)









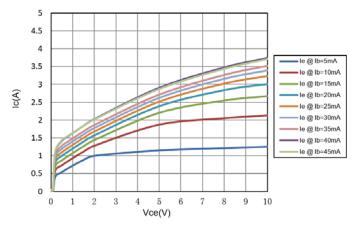
Electrical Characteristics (@ $T_A = \pm 25^{\circ}C$, unless otherwise specified.)

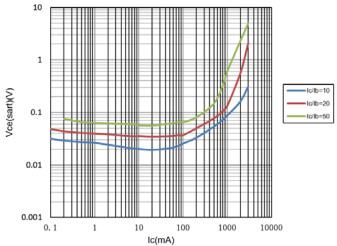
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	-100	_	_	>	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	-100	_	_	٧	$I_C = -10mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	_	_	>	$I_E = -100 \mu A$
Collector-Base Cutoff Current	I _{CBO}	_	_	-100	nA	V _{CB} = -80V
Collector-base Cuton Current		_	_	-50	μΑ	V _{CB} = -80V @Tj = 150°C
Emitter Cutoff Current	I _{EBO}	_	_	-100	nA	V _{EB} = -7V
Collector-Emitter Cutoff Current	I _{CES}	_	_	-100	nA	V _{CES} = -80V
ON CHARACTERISTICS (Note 9)						
		170	305	_		I _C = -500mA, V _{CE} = -10V
DC Current Gain	h	160	275	_		$I_C = -1A$, $V_{CE} = -10V$
DC Curient Gain	h _{FE}	45	90	_		$I_C = -2A$, $V_{CE} = -10V$
		10	20	_		$I_C = -3A$, $V_{CE} = -10V$
Collector-Emitter Saturation Voltage	\/· .	_	-70	-110	mV	$I_C = -0.5A, I_B = -50mA$
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_	-220	-360		$I_C = -2A$, $I_B = -200mA$
Collector-Emitter Saturation Resistance	R _{CE(sat)}	_	110	180	mΩ	$I_C = -2A$, $I_B = -200mA$
Base-Emitter Saturation Voltage	V _{BE(sat)}	_	-0.91	-1	V	$I_C = -1A$, $I_B = -50mA$
Base-Emilier Saturation voltage		_	-1.02	-1.2		$I_C = -2A$, $I_B = -200mA$
Base-Emitter Turn-On Voltage	V _{BE(on)}	_	-0.68	-0.9	>	$I_C = -0.1A, V_{CE} = -2V$
SMALL SIGNAL CHARACTERISTICS						
Current Gain-Bandwidth Product	f _T	_	125	_	MHz	$V_{CE} = -10V, I_{C} = -100mA, f = 100MHz$
Output Capacitance	C _{obo}	_	30	_	pF	$V_{CB} = -10V$, $f = -1MHz$
Delay Time	t _d	_	20	_	ns	
Rise Time	t _r	_	180	_	ns	
Turn-On Time	t _(on)	_	200	_	ns	$V_{CC} = -12.5V, I_{C} = -1A$
Storage Time	ts	_	350	_	ns	$I_{B1} = -I_{B2} = 50 \text{mA}$
Fall Time	t _f	_	220	_	ns	
Turn-Off Time	t _(off)	_	570	_	ns	

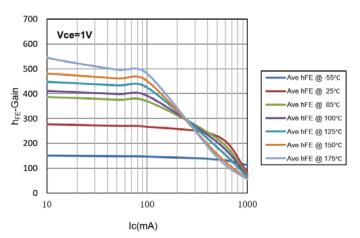
Note: 9. Measured under pulsed conditions. Pulse width $\leq 300 \mu s$. Duty cycle $\leq 2\%$.

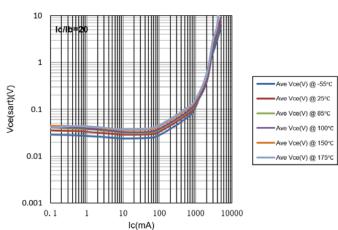


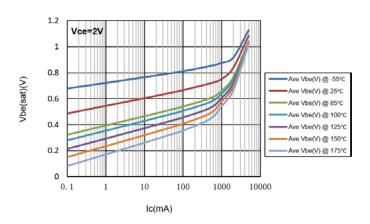
Electrical Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

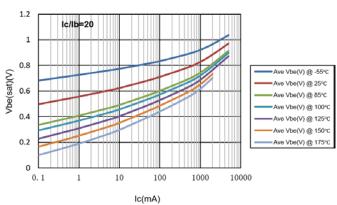










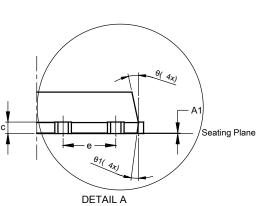




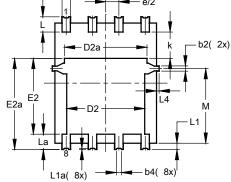
Package Outline Dimensions

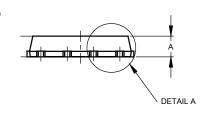
Please see http://www.diodes.com/package-outlines.html for the latest version.

D1 D1 1.900 D1 1.400 Ø0.986 Depth 0.07±0.030



PowerDI5060-8 (SWP) (Type Q)



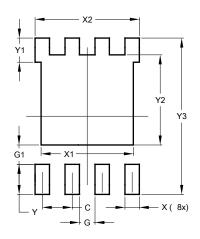


PowerDI5060-8 (SWP)						
(Type Q)						
Dim	Min Max		Тур			
Α	0.90	1.10	1.00			
A1	0	0.05	_			
b	0.30	0.50	0.41			
b2	0.20	0.35	0.25			
b4	().25REF	-			
C	0.230	0.330	0.277			
D		.15 BS0)			
D1	4.70	5.10	4.90			
D2	3.56	3.96	3.76			
D2a	3.78	4.18	3.98			
Е	6	.40 BS0)			
E1	5.60	6.00	5.80			
E2	3.46	3.86	3.66			
E2a	4.195	4.595	4.395			
е	1.27BSC					
k	1.05	_	_			
L	0.635	0.835	0.735			
La	0.635	0.835	0.735			
L1	0.200	0.400	0.300			
L1a	0.050REF					
L4	0.025	0.225	0.125			
M	3.205	4.005	3.605			
θ	10°	12°	11°			
θ1	6°	8°	7°			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (SWP) (Type Q)



Dimensions	Value (in mm)		
С	1.270		
G	0.660		
G1	0.820		
Х	0.610		
X1	4.100		
X2	4.420		
Υ	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2018, Diodes Incorporated

www.diodes.com